

**2SB1519**

Preliminary

**Silicon PNP Epitaxial  
High Voltage Amplifier****Features**

- Low saturation voltage  
 $V_{CE}(\text{sat}) \leq -0.3 \text{ V}$
- Large current capacitance  
 $I_C = -2 \text{ A}$

**Table 1 Absolute Maximum Ratings**  
(Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V <sub>CBO</sub>	-50	V
Collector to emitter voltage	V <sub>CEO</sub>	-50	V
Emitter to base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-2	A
Peak collector current	i <sub>C(peak)</sub> *	-3	A
Collector power dissipation	P <sub>C</sub> **	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 ms, duty cycle ≤ 20%

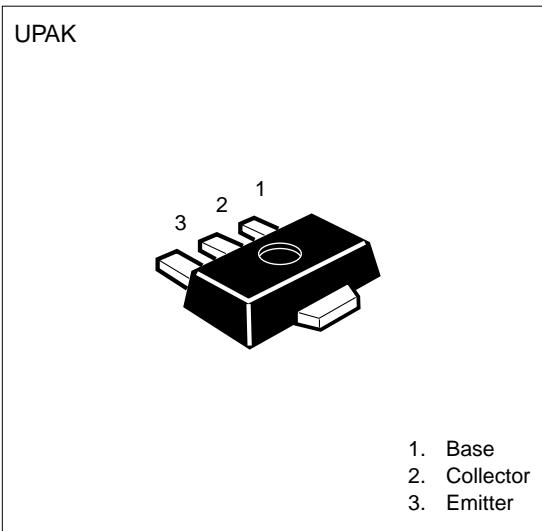
\*\* When using the alumina ceramic board (12.5 × 20 × 0.7 mm)

**Table 2 Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	-50	—	—	V	I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	-50	—	—	V	I <sub>C</sub> = -1 mA, R <sub>BE</sub> = ∞
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	-5	—	—	V	I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0
Collector cutoff current	I <sub>CBO</sub>	—	—	-1	μA	V <sub>CB</sub> = -40 V, I <sub>E</sub> = 0
Collector cutoff current	I <sub>CEO</sub>	—	—	-5	μA	V <sub>CE</sub> = -40 V, R <sub>BE</sub> = ∞
Emitter cutoff current	I <sub>EBO</sub>	—	—	-1	μA	V <sub>EB</sub> = -4 V, I <sub>C</sub> = 0
DC current transfer ratio	h <sub>FE</sub> 1	120	—	300	—	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A*
DC current transfer ratio	h <sub>FE</sub> 2	40	—	—	—	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1.5 A*
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	-0.3	V	I <sub>C</sub> = -1 A, I <sub>B</sub> = -50 mA*
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	—	—	-1.2	V	I <sub>C</sub> = -1 A, I <sub>B</sub> = -50 mA*

\* Pulse test

\*\* Marking is "FS".



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